



8N170

Preliminary

Power MOSFET

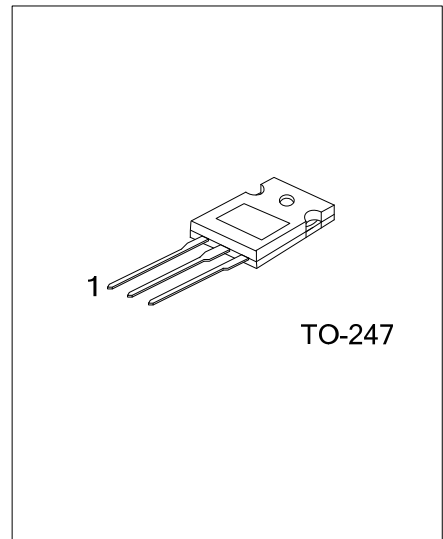
8.0A, 1700V N-CHANNEL POWER MOSFET

DESCRIPTION

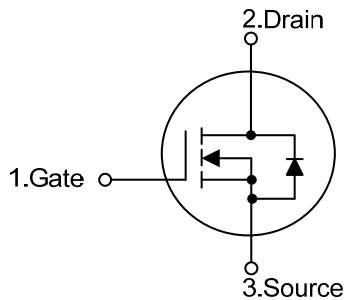
The UTC **8N170** provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} \leq 2.7 \Omega @ V_{GS}=10V, I_D=4.0A$
- * Low Reverse Transfer Capacitance
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness



SYMBOL



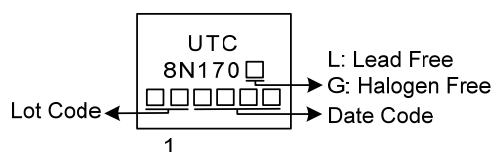
ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|--------------|---------|----------------|---|---|---------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 8N170L-T47-T | 8N170G-T47-T | TO-247 | G | D | S | Tube |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|---|--|
| <p>8N170G-T47-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p> | <p>(1) T: Tube</p> <p>(2) T47: TO-247</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p> |
|---|--|

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------------------------|------------------------|------------------|------------|------|
| Drain-Source Voltage | | V _{DSS} | 1700 | V |
| Gate-Source Voltage | | V _{GSS} | ±30 | V |
| Drain Current | Continuous | I _D | 8 | A |
| | Pulsed (Note 2) | I _{DM} | 16 | A |
| Avalanche Energy | Single Pulsed (Note 3) | E _{AS} | 552 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 5.94 | V/ns |
| Power Dissipation | | P _D | 320 | W |
| Junction Temperature | | T _J | +150 | °C |
| Storage Temperature | | T _{STG} | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 100mH, I_{AS} = 3.32A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C

4. I_{SD} ≤ 8.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|-----------------|---------|------|
| Junction to Ambient | θ _{JA} | 50 | °C/W |
| Junction to Case | θ _{JC} | 0.39 | °C/W |

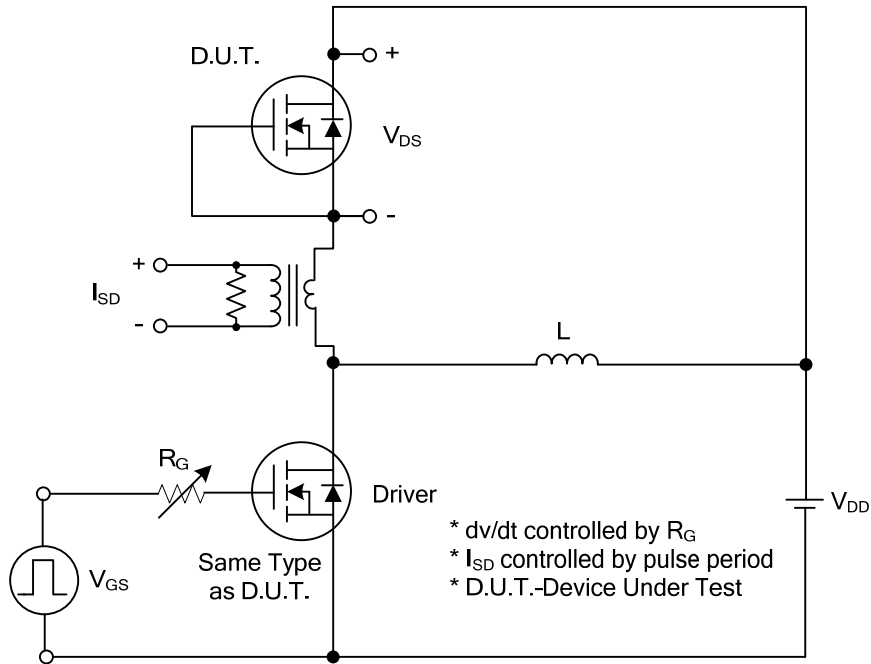
■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---------------------|---|------|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250μA | 1700 | | | V |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =1700V, V _{GS} =0V | | | 10 | μA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±30V, V _{DS} =0V | | | ±100 | nA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | V _{DS} =V _{GS} , I _D =250μA | 3.0 | | 5.0 | V |
| Static Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =4.0A | | | 2.7 | Ω |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C _{ISS} | V _{DS} =25V, V _{GS} =0V, f=1MHz | | 3756 | | pF |
| Output Capacitance | C _{OSS} | | | 313 | | pF |
| Reverse Transfer Capacitance | C _{RSS} | | | 73 | | pF |
| SWITCHING CHARACTERISTICS | | | | | | |
| Total Gate Charge (Note 1) | Q _G | V _{DS} =1360V, V _{GS} =10V, I _D =8.0A (Note 1, 2) | | 147 | | nC |
| Gate-Source Charge | Q _{GS} | | | 19 | | nC |
| Gate-Drain Charge | Q _{GD} | | | 22 | | nC |
| Turn-On Delay Time (Note 1) | t _{D(ON)} | V _{DD} =100V, V _{GS} =10V, I _D =8.0A, R _G =25Ω (Note 1, 2) | | 69 | | ns |
| Turn-On Rise Time | t _R | | | 80 | | ns |
| Turn-Off Delay Time | t _{D(OFF)} | | | 423 | | ns |
| Turn-Off Fall Time | t _F | | | 86 | | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | | | | 8 | A |
| Maximum Pulsed Drain-Source Diode Forward Current | I _{SM} | | | | 16 | A |
| Drain-Source Diode Forward Voltage (Note 1) | V _{SD} | I _S =8.0A, V _{GS} =0V | | | 1.4 | V |
| Body Diode Reverse Recovery Time (Note 1) | t _{rr} | I _S =8.0A, V _{GS} =0V, | | 1312 | | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | di _F /dt=100A/μs | | 24 | | μC |

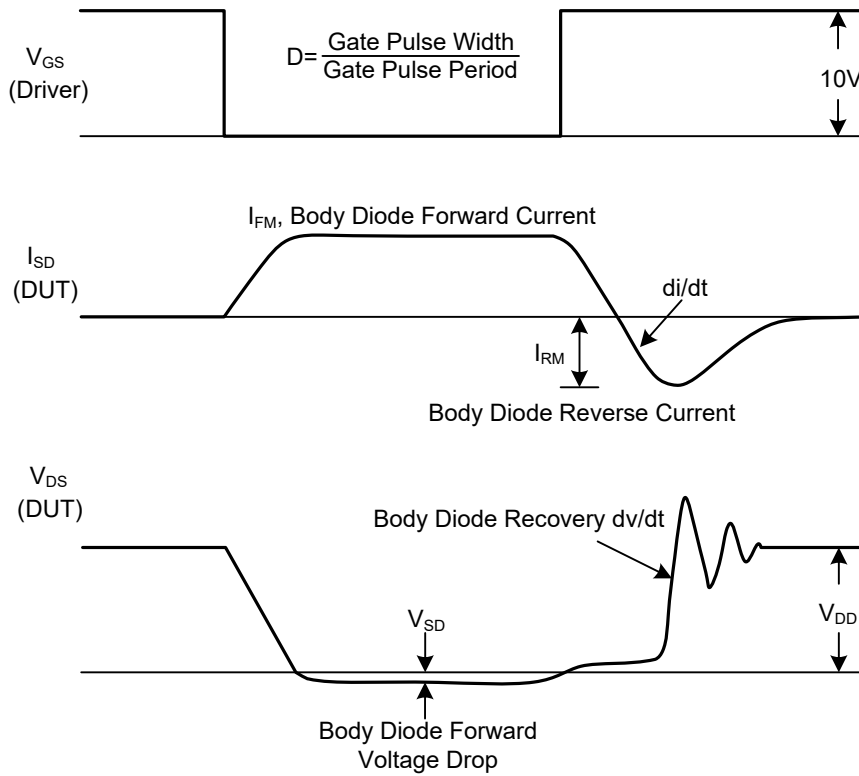
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

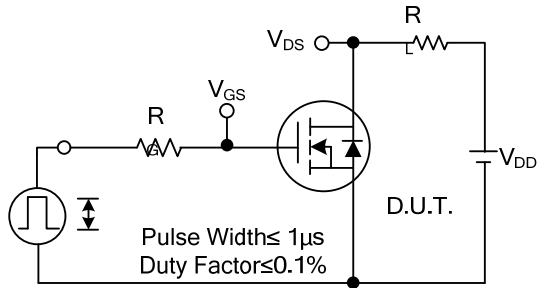


Peak Diode Recovery dv/dt Test Circuit

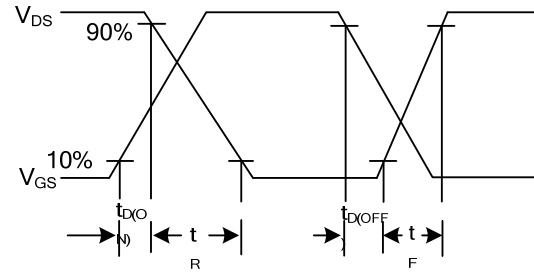


Peak Diode Recovery dv/dt Waveforms

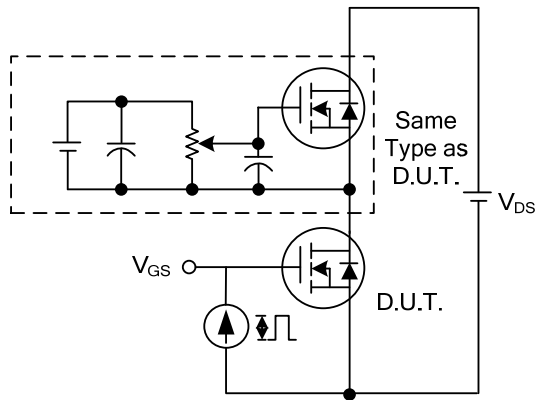
■ TEST CIRCUITS AND WAVEFORMS



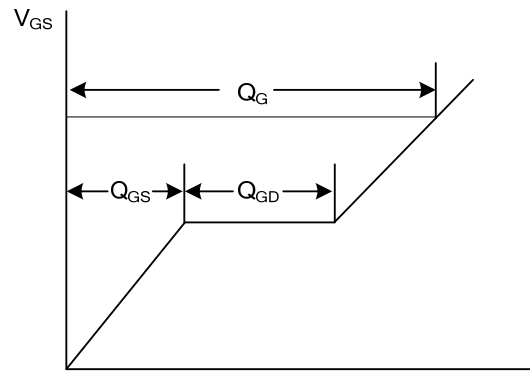
Switching Test Circuit



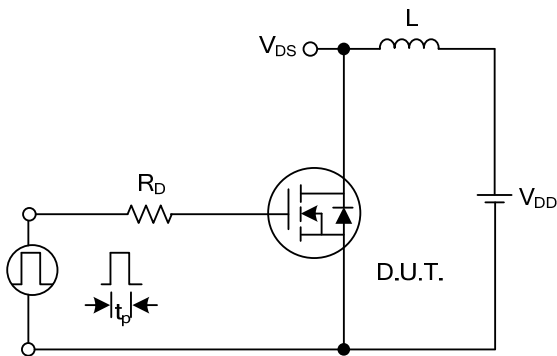
Switching Waveforms



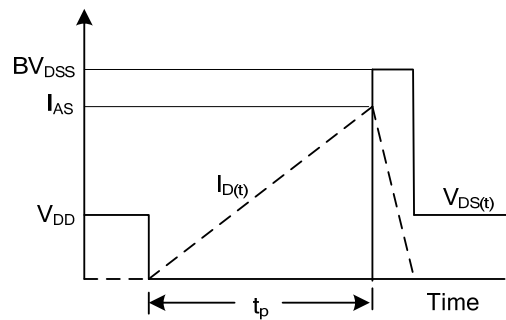
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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